



DCX53/-16

PNP SURFACE MOUNT TRANSISTOR

Features

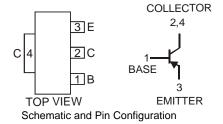
- Epitaxial Planar Die Construction
- Complementary NPN Type Available (DCX56)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)



SOT89-3L



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-100	V
Collector-Emitter Voltage	V _{CEO}	-80	V
Emitter-Base Voltage	V _{EBO}	-5	V
Peak Pulse Current	I _{CM}	-1.5	A
Continuous Collector Current	Ic	-1	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P_{D}	1	W
Thermal Resistance, Junction to Ambient Air @ T _A = 25°C (Note 3)	$R_{ hetaJA}$	125	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Electrical Characteristics @TA = 25°C unless otherwise specified

Charac	teristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)							
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	-100	_	_	V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	-80	_	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	-5			V	$I_E = -10\mu A, I_C = 0$
Collector Cutoff Current		І _{СВО}	_	_	-100 -20	nA μA	$V_{CB} = -30V, I_E = 0$ $V_{CB} = -30V, I_E = 0, T_A = 150$ °C
Emitter Cutoff Current		I _{EBO}	_	_	-100	nA	V _{EB} = -5V, I _C = 0
ON CHARACTERISTICS (No	ON CHARACTERISTICS (Note 4)						
Collector-Emitter Saturation Voltage		V _{CE(SAT)}		_	-0.5	V	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Turn-On Voltage		V _{BE(SAT)}	_	_	-1.0	V	$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$
DO 0	DCX53, DCX53-16		63 40				$I_C = -5mA$, $V_{CE} = -2V$ $I_C = -500mA$, $V_{CE} = -2V$
DC Current Gain	DCX53	h _{FE}	63	_	250		I _C = -150mA, V _{CE} = -2V
	DCX53-16		100	_	250		I _C = -150mA, V _{CE} = -2V
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product		f _T		200		MHz	$I_C = -50 \text{mA}, V_{CE} = -5 \text{V},$ f = 100MHz
Output Capacitance		C_{obo}		_	25	pF	$V_{CB} = -10V$, $f = 1MHz$

Notes:

- 1. No purposefully added lead
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 4. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.



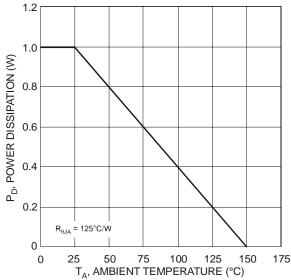


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

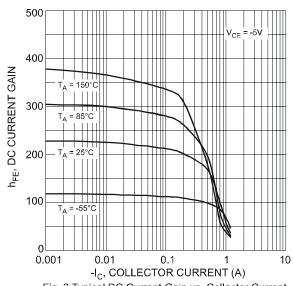


Fig. 3 Typical DC Current Gain vs. Collector Current

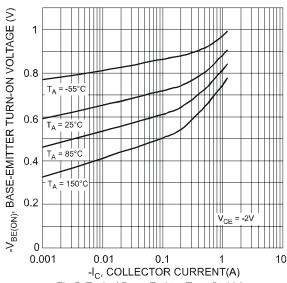
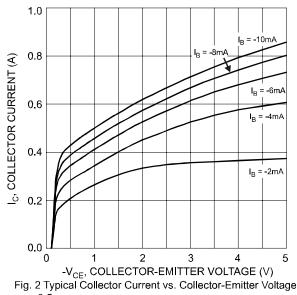
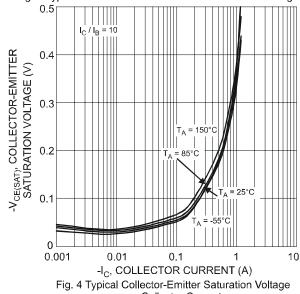


Fig 5. Typical Base-Emitter Turn-On Voltage vs. Collector Current





vs. Collector Current

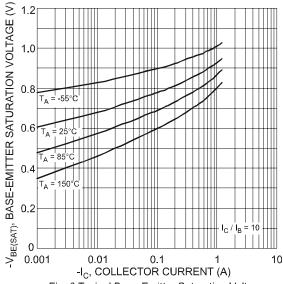
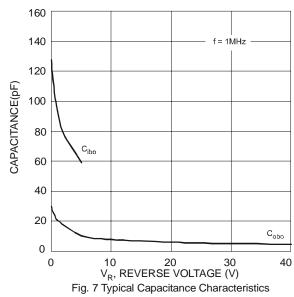


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current





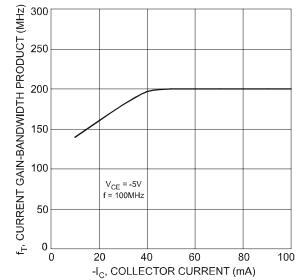


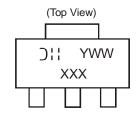
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DCX53-13	SOT89-3L	2500/Tape & Reel
DCX53-16-13	SOT89-3L	2500/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf.

Marking Information

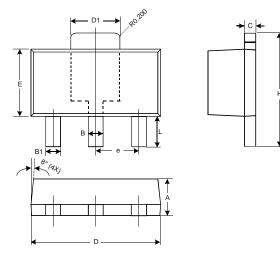


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XXX = Product type marking code if

YWW = Date code marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52 P18 = DCX53 P18-16 = DCX53 -16

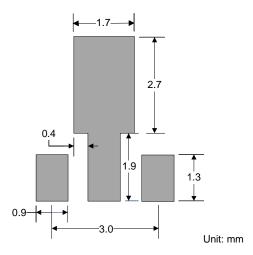
Package Outline Dimensions



SOT89-3L					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.45	0.55	0.50		
B1	0.37	0.47	0.42		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.50	1.70	1.60		
Е	2.40	2.60	2.50		
е	_	_	1.50		
Н	3.95	4.25	4.10		
L	0.90	1.20	1.05		
All Dimensions in mm					



Suggested Pad Layout



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